



#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	Max R <sub>DS(on)</sub>	Max I <sub>D</sub> T <sub>A</sub> = +25°C (Note 5)
100V	230mΩ @ V <sub>GS</sub> = 10V	1.9A
1007	300mΩ @ V <sub>GS</sub> = 4.5V	1.68A

### **Features and Benefits**

- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- SOT26 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

### **Description and Applications**

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes it ideal for high-efficiency, low-voltage, power-management applications.

- DC-DC converters
- Power-management functions
- Disconnect switches
- Motor controls

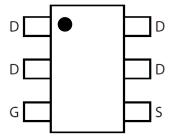
#### **Mechanical Data**

- Package: SOT26
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.015 grams (Approximate)

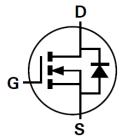




Top View



Pinout Top View



Device Symbol

### Ordering Information (Note 4)

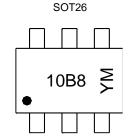
Part Number	Part Number Package Reel Size (inch) Tape Width (mm)		Package [	Pac	king
Fait Number	Package	Reel Size (Ilicii)	rape widin (iiiii)	Qty.	Carrier
ZXMN10B08E6TA	SOT26	7	8	3,000	Reel
ZXMN10B08E6TC	SOT26	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- 5. For a device surface-mounted on FR4 PCB measured at  $t \le 5$  secs.



## **Marking Information**



10B8 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: L = 2024) M or  $\overline{M}$  = Month (ex: 9 = September)

#### Date Code Key

Year	2014	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	В	-	L	М	N	Р	R	S	Т	U	V	W
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

#### Maximum Ratings (@TA = +25°C, unless otherwise specified.)

CI	naracteristic		Symbol	Value	Unit
Drain-Source Voltage			VDSS	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
		(Note 5)		1.9	
Continuous Drain Current	Vgs = 10V	T <sub>A</sub> = +70°C (Note 5)	l <sub>D</sub>	1.5	Α
		(Note 6)		1.6	
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	9	Α
Continuous Source Current (Bo	(Note 5)	Is	2.5	Α	
Pulsed Source Current (Body D	Diode)	(Note 7)	Ism	9	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

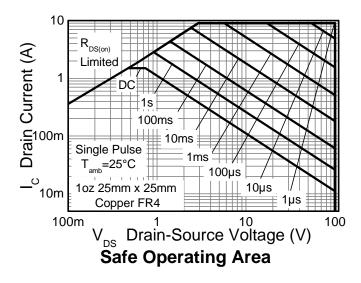
Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)		1.1	W	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	8.8	mW/°C	
Power Dissipation	(Note 5)	D-	1.7	W	
Linear Derating Factor	(Note 5)	PD	13.6	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 6)	D	113	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	- R <sub>θJA</sub>	73	- °C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

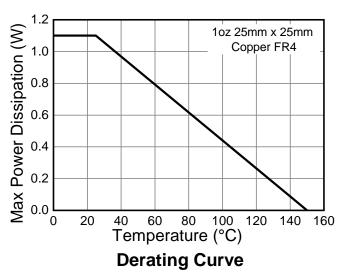
Notes:

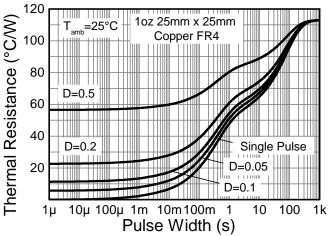
- 5. For a device surface-mounted on FR4 PCB measured at t  $\leq$  5 secs.
- $6. \ For a \ device surface-mounted on 25mm \ x \ 25mm \ FR4 \ PCB \ with \ high \ coverage \ of single \ sided \ 1oz \ copper, \ in \ still \ air \ conditions.$
- 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature. Refer to *Transient Thermal Impedance* graph.

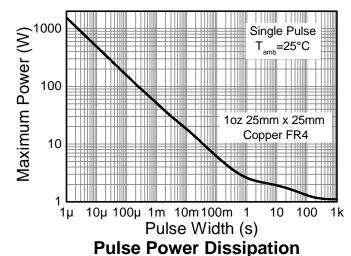


#### **Thermal Characteristics**









**Transient Thermal Impedance** 



# **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

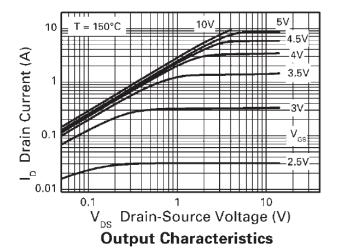
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS			•	•	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	IDSS	_	_	0.5	μΑ	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	VGS(th)	1.0	_	3.0	V	I <sub>D</sub> = 250µA, V <sub>DS</sub> = V <sub>GS</sub>
				0.23		VGS = 10V, ID = 1.6A
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(on)</sub>	_	_	0.30	Ω	$V_{GS} = 4.5V, I_D = 1.4A$
				0.50		V <sub>G</sub> S = 4.3V, I <sub>D</sub> = 1.1A
Forward Transconductance (Notes 8 & 9)	<b>G</b> fs		4.8	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 1.6A
Diode Forward Voltage (Note 8)	VsD	_	0.85	0.95	V	T <sub>J</sub> = +25°C, I <sub>S</sub> = 2.0A, V <sub>GS</sub> = 0V
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	497	_	pF	
Output Capacitance	Coss	_	29	_	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V - f = 1.0MHz
Reverse Transfer Capacitance	Crss		18	_	pF	1 – 1.00112
Gate Charge (Note 10)	$Q_g$	_	5.0	_	nC	$V_{DS} = 50V, V_{GS} = 5V, I_{D} = 1.6A$
Total Gate Charge (Note 10)	Qg		9.2	_	nC	1/ 50/// 40//
Gate-Source Charge (Note 10)	Qgs		1.7	_	nC	$V_{DS} = 50V, V_{GS} = 10V$ $V_{DS} = 1.6A$
Gate-Drain Charge (Note 10)	$Q_{gd}$	_	2.5	_	nC	1D = 1.0A
Turn-On Delay Time (Note 10)	td(on)	_	2.9	_	ns	
Turn-On Rise Time (Note 10)	tr	_	2.1	_	ns	V <sub>DD</sub> = 50V, I <sub>D</sub> = 1.0A
Turn-Off Delay Time (Note 10)	td(off)	_	12.1	_	ns	$R_G \cong 6.0\Omega$ , $V_{GS} = 10V$
Turn-Off Fall Time (Note 10)	t <sub>f</sub>		5.0	_	ns	7
Reverse Recovery Time	t <sub>rr</sub>		32	_	ns	T <sub>J</sub> = +25°C, I <sub>F</sub> = 1.7A
Reverse Recovery Charge	Qrr		40	_	nC	di/dt = 100A/µs

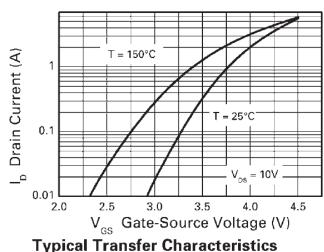
Notes:

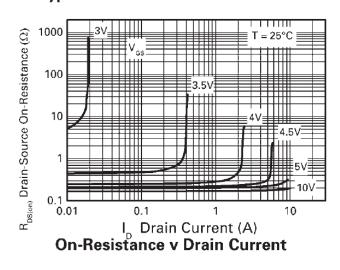
- 8. Measured under pulsed conditions. Width ≤ 300µs. Duty cycle ≤ 2%.
  9. For design aid only, not subject to production testing.
  10. Switching characteristics are independent of operating junction temperature.

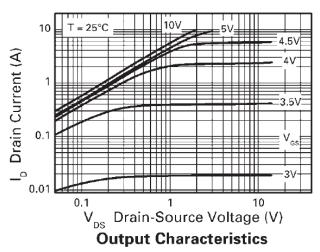


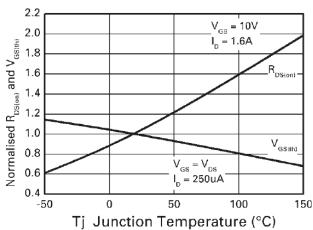
# **Typical Characteristics**



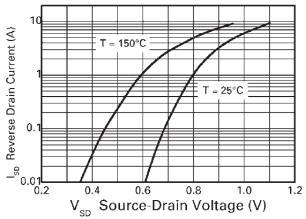








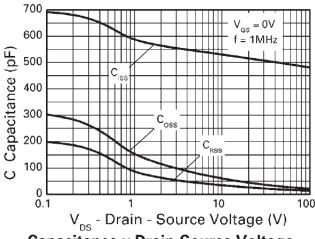
# **Normalised Curves v Temperature**



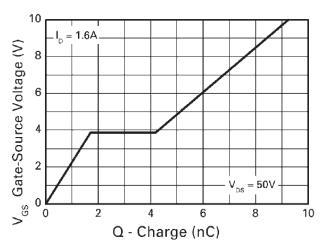
Source-Drain Diode Forward Voltage



# Typical Characteristics (continued)

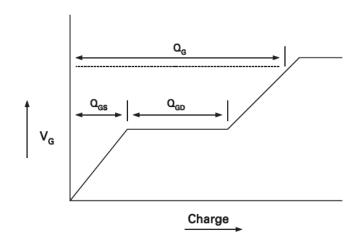


Capacitance v Drain-Source Voltage

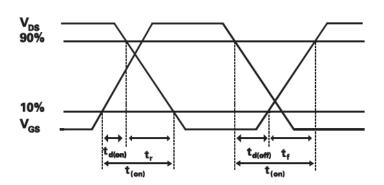


Gate-Source Voltage v Gate Charge

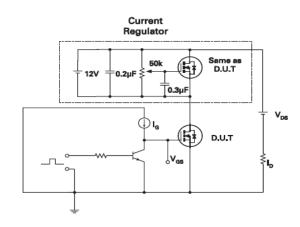
## **Test Circuits**



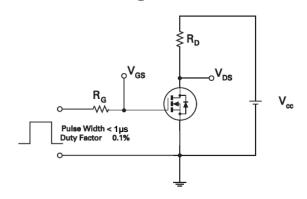
**Basic Gate Charge Waveform** 



**Switching Time Waveforms** 



## **Gate Charge Test Circuit**

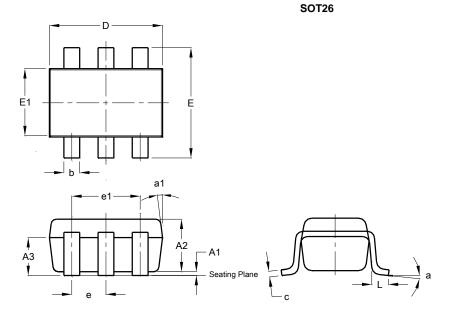


**Switching Time Test Circuit** 



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

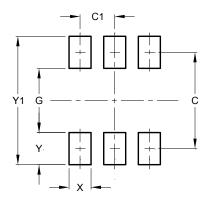


	SOT26						
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
E	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	Dimen	sions	in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
V1	3.20



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